

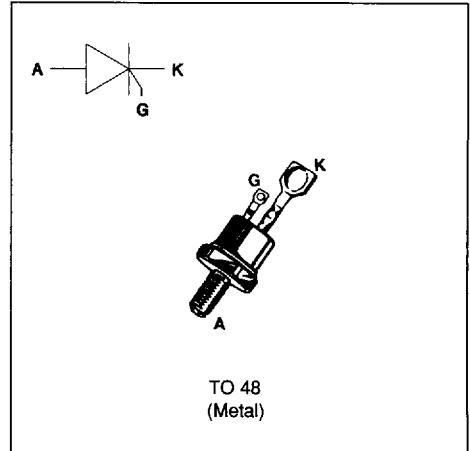
FEATURES

- HIGH SURGE CAPABILITY
- HIGH ON-STATE CURRENT
- HIGH STABILITY AND RELIABILITY

DESCRIPTION

The BTW 48 Family of Silicon Controlled Rectifiers uses a high performance glass passivated technology.

This general purpose Family of Silicon Controlled Rectifiers is designed for power supplies up to 400Hz on resistive or inductive load.


ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	$T_c = 85^\circ C$ 50	A
$I_T(AV)$	Average on-state current (180° conduction angle, single phase circuit)	$T_c = 85^\circ C$ 32	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)	$t_p = 8.3$ ms	520
		$t_p = 10$ ms	500
I^2t	I^2t value	$t_p = 10$ ms	1250
di/dt	Critical rate of rise of on-state current Gate supply : $I_G = 600$ mA $di_G/dt = 1$ A/ μ s	100	A/ μ s
T_{stg} T_j	Storage and operating junction temperature range	- 40 to + 150 - 40 to + 125	°C °C
T_l	Maximum lead temperature for soldering during 10 s at 4.5 mm from case	230	°C

Symbol	Parameter	BTW 48-					Unit
		200	400	600	800	1200	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ C$	200	400	600	800	1200	V

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth (c-h)	Contact (case to heatsink)	0.4	°C/W
Rth (j-c) DC	Junction to case for DC	0.7	°C/W

GATE CHARACTERISTICS (maximum values)

PG (AV) = 1W PGM = 60W (tp = 20 μs) IFGM = 10A (tp = 20 μs) VFGM = 16V (tp = 20 μs) VRGM = 5 V.

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Value	Unit	
IGT	V _D =12V (DC) R _L =33Ω	T _j =25°C	MAX	60	mA
VGT	V _D =12V (DC) R _L =33Ω	T _j =25°C	MAX	1.5	V
VGD	V _D =V _{DRM} R _L =3.3kΩ	T _j = 125°C	MIN	0.2	V
tgt	V _D =V _{DRM} I _G = 200mA dI _G /dt = 1.5A/μs	T _j =25°C	TYP	2	μs
I _L	I _G = 1.2 IGT	T _j =25°C	TYP	60	mA
I _H	I _T = 500mA gate open	T _j =25°C	TYP	30	mA
V _{TM}	I _{TM} = 100A tp = 380μs	T _j =25°C	MAX	1.8	V
I _{DRM} I _{RRM}	V _{DRM} Rated V _{RRM} Rated	T _j =25°C	MAX	0.02	mA
		T _j = 125°C		6	
dV/dt	Linear slope up to V _D =67%V _{DRM} gate open	T _j = 125°C	MIN	200	V/μs
T _q	V _D =67%V _{DRM} I _{TM} = 100A V _R = 50V dI _{TM} /dt = 30 A/μs dV _D /dt = 20V/μs	T _j = 125°C	TYP	100	μs

Fig.1 : Maximum average power dissipation versus average on-state current.

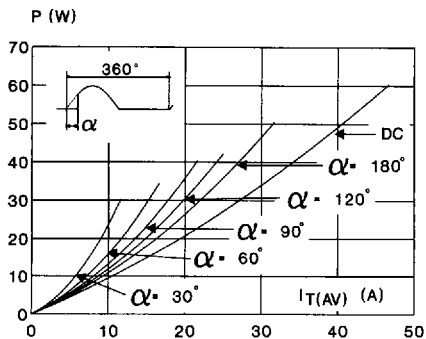


Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

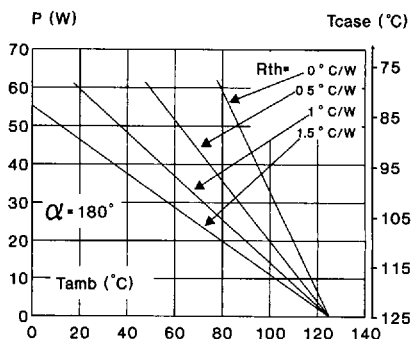


Fig.3 : Average on-state current versus case temperature.

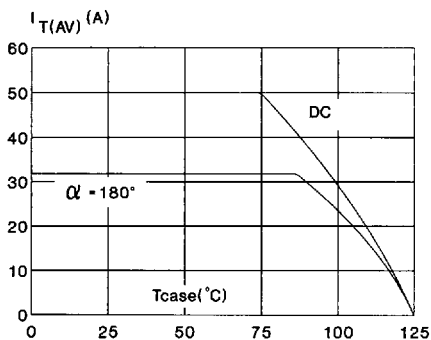


Fig.4 : Thermal transient impedance junction to ambient versus pulse duration.

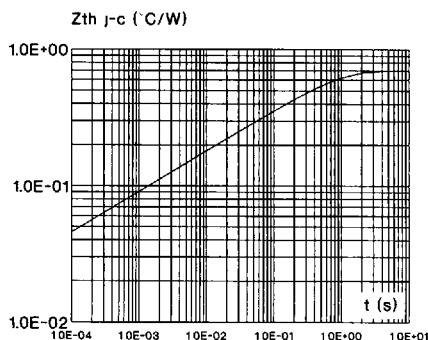


Fig.5 : Relative variation of gate trigger current versus junction temperature.

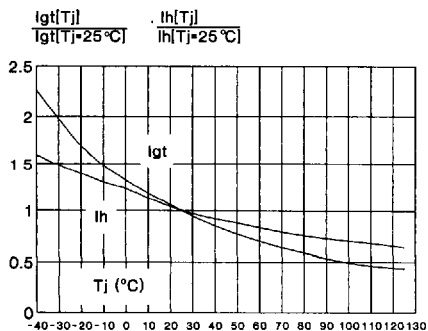


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.

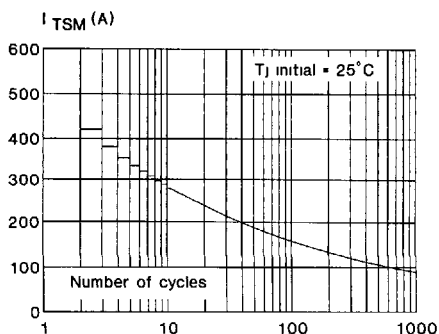


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10$ ms, and corresponding value of I^2t .

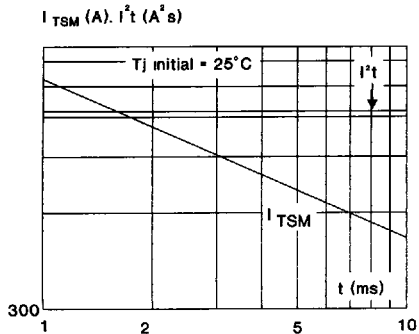
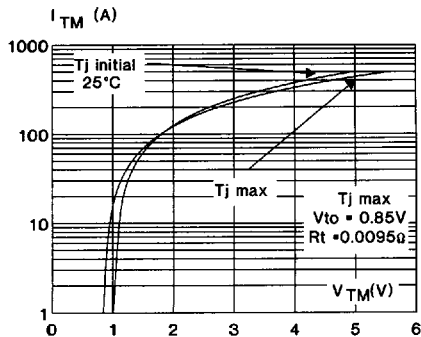
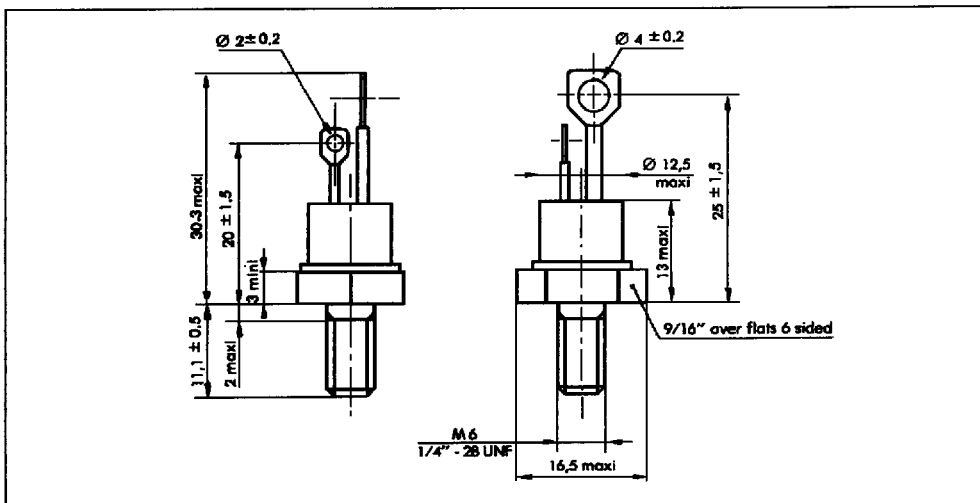


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA (in millimeters)

TO 48 Metal



Cooling method : A
 Marking : type number
 Weight : 13.5 g
 Polarity : Anode (or A2) to case
 Stud torque : 3.5 mAN min / 3.8 mAN max